TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

2SA1242

Strobe Flash Applications Medium Power Amplifier Applications

- Excellent hFE linearity
 - : hFE (1) = 100 to 320 (VCE = -2 V, IC = -0.5 A)
 - $h_{FE}(2) = 70 \text{ (min) } (V_{CE} = -2 \text{ V}, I_{C} = -4 \text{ A})$
- Low collector saturation voltage
 - : $V_{CE (sat)} = -1.0 \text{ V (max) (IC} = -4 \text{ A, IB} = -0.1 \text{ A)}$
- · High power dissipation
 - $: PC = 10 \text{ W (Tc} = 25^{\circ}\text{C)}, PC = 1.0 \text{ W (Ta} = 25^{\circ}\text{C)}$

Absolute Maximum Ratings (Ta = 25°C)

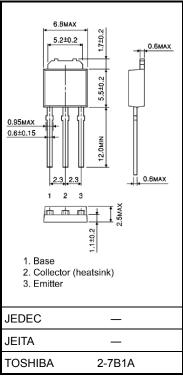
Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	-35	٧	
Collector-emitter voltage		V _{CEO}	-20	٧	
Emitter-base voltage		V _{EBO}	-8	V	
Collector current	DC	Ic	- 5	А	
	Pulsed (Note 1)	I _{CP}	-8		
Base current		ΙΒ	-0.5	Α	
Collector power dissipation	Ta = 25°C	PC	1.0	W	
	Tc = 25°C	FC	10		
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Note 1: Pulse test: Pulse width = 10 ms (max), duty cycle = 30% (max)

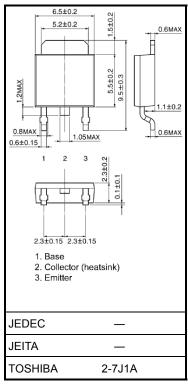
Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Unit: mm



Weight: 0.36 g (typ.)



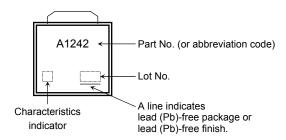
Weight: 0.36 g (typ.)

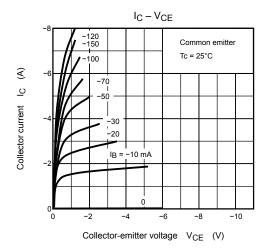
Electrical Characteristics (Ta = 25°C)

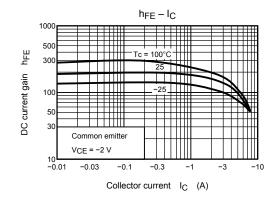
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = -35 \text{ V}, I_E = 0$	_	_	-100	nA
Emitter cut-off current	I _{EBO}	V _{EB} = -8 V, I _C = 0	_	_	-100	nA
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -10 \text{ mA}, I_B = 0$	-20	_	_	٧
Emitter-base breakdown voltage	V _{EBO}	$I_E = -1 \text{ mA}, I_C = 0$	-8	_	_	V
DC current gain	h _{FE (1)} (Note 3)	V _{CE} = -2 V, I _C = -0.5 A	100	_	320	
	h _{FE (2)}	V _{CE} = -2 V, I _C = -4 A	70	_	_	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = -4 A, I _B = -0.1 A	_	_	-1.0	V
Base-emitter voltage	V_{BE}	V _{CE} = -2 V, I _C = -4 A	_	_	-1.5	V
Transition frequency	f _T	V _{CE} = -2 V, I _C = -0.5 A	_	170	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = -10 V, I _E = 0, f = 1 MHz	_	62	_	pF

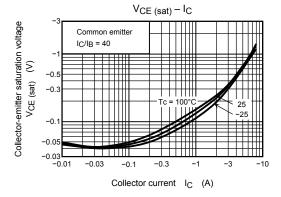
Note 3: $h_{FE\ (1)}$ classification O: 100 to 200, Y: 160 to 320

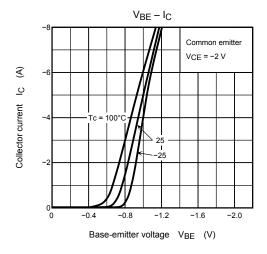
Marking

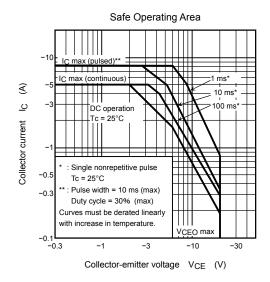


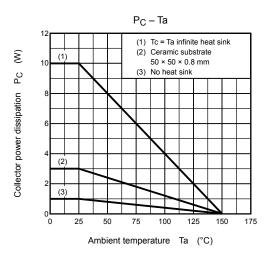












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